

Radiation-Hard Silicon Carbide Dosimeters for Electron and Proton FLASH QA

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3 Institut Curie

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Outline

- Introduction: FLASH radiotherapy
- Devices fabricated at IMB-CNM
- Dosimetry in UHDR beams
 - Electrons
 - Protons
 - Radiation hardness tests
 - Spatially resolved dosimetry
- Conclusions

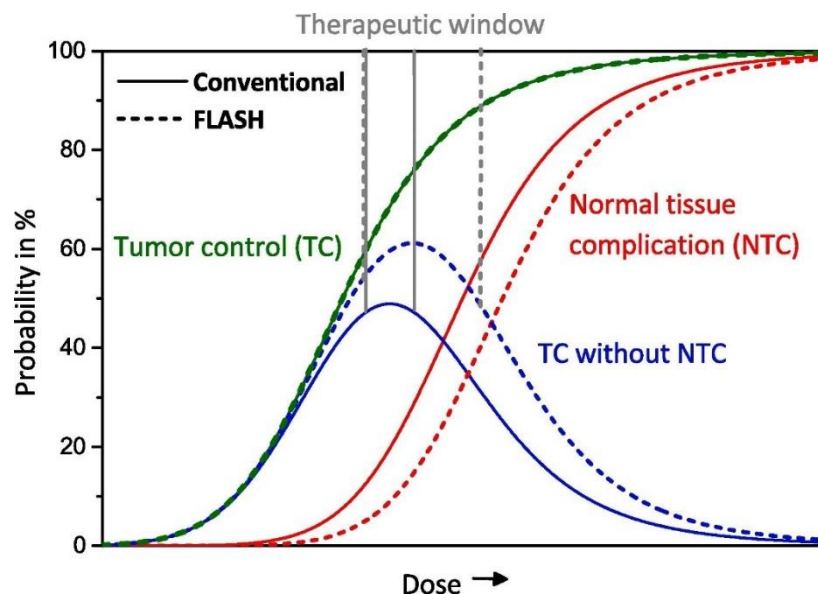
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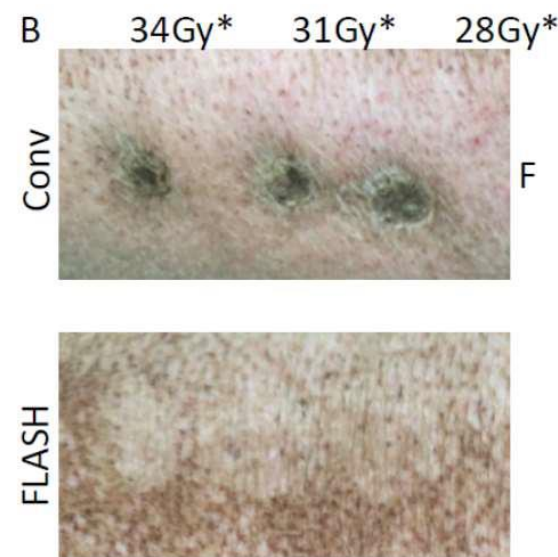
FLASH effect (*Favaudon et al., Sci Transl Med 6 (2014)*):

Irradiations with **Ultra-High Dose Rate (UHDR) pulsed radiation** reduce adverse effects in healthy tissues

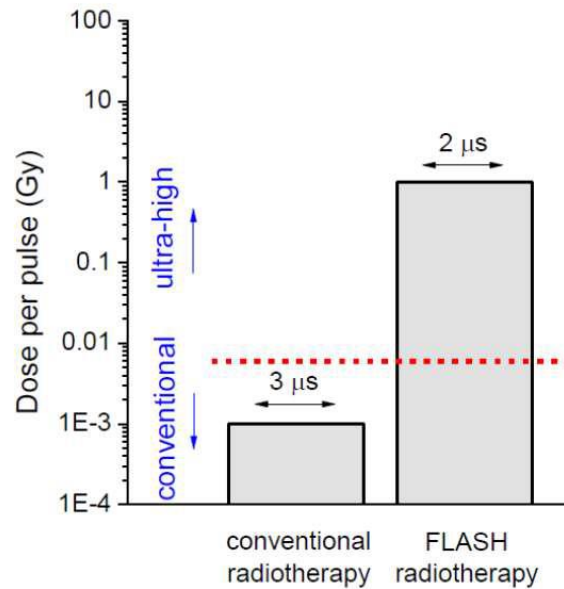
FLASH dose rate ≥ 40 Gy/s (conventional radiotherapy ≈ 0.05 Gy/s)



Schüller et al., Physica Medica 80 (2020)



Vozenin et al., Clin Cancer Res 25 (2019)



w	pulse width	$[0.5 - 2.2] \mu\text{s}$
f	pulse repetition frequency	$[10 - 200] \text{ Hz}$
D_p^*	dose-rate in pulse	$[10^3 - 5 \cdot 10^6] \text{ Gy/s}$
$D_p = D_p^* \cdot w$	dose per pulse	$[10^{-3} - 5] \text{ Gy}$
$D_m^* = D_p^* \cdot w \cdot f$	mean dose-rate	$[10^{-2} - 1000] \text{ Gy/s}$

1 Gy in water of 160 MeV
 protons $\approx$ **1E9 p/cm²**
per pulse of $\sim 1 \mu\text{s}$

(dose = fluence $\times$ mass stopping power)



- Saturation of conventional active dosimeters (gas and silicon)
- Need **real-time, precise, radiation hard dosimeters: SiC**

Why SiC?

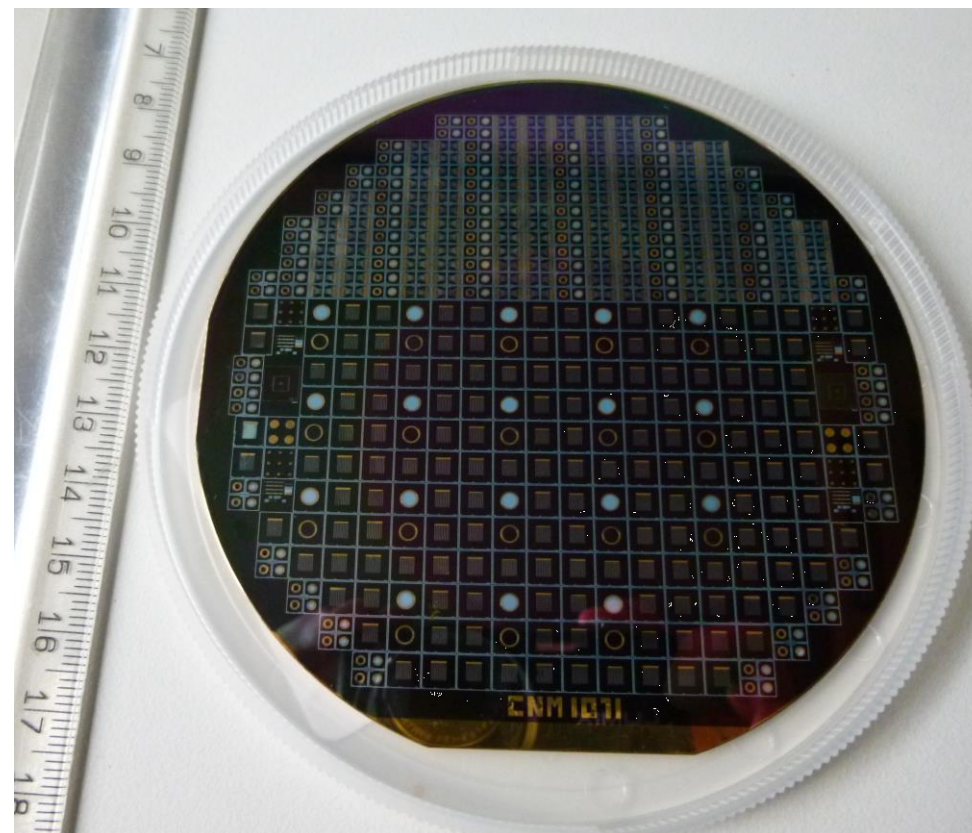
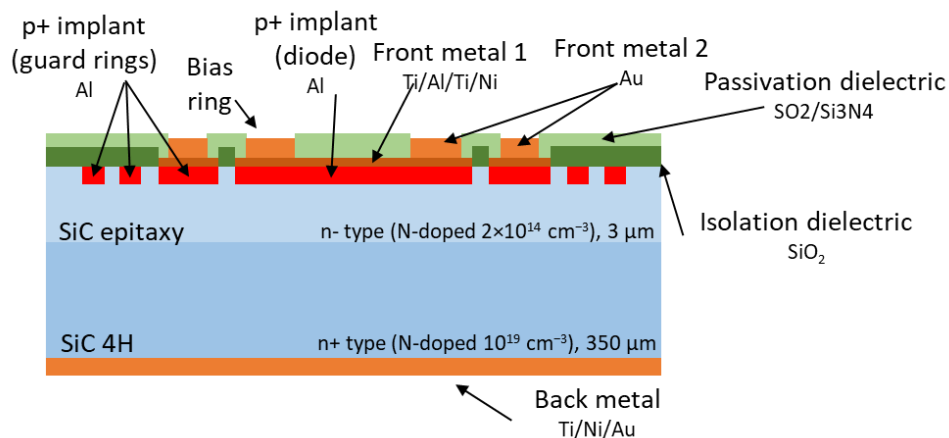
	Silicon	4H-SiC	CVD diamond
Band gap [eV]	1.12	3.23	5.5
Ionization energy [eV/e-h]	3.6	7.6 – 8.4	13.6
Atomic displacement threshold [eV]	13-15	30 – 40	43
Density [g/cm ³]	2.33	3.22	3.52
Electron mobility [cm ² /Vs]	1450	800 – 900	1700
Hole mobility [cm ² /Vs]	450	115	2100
Electr. sat. velocity [1E7 cm/s]	1	2.2	2.7
Breakdown field [MV/cm]	0.3	3 – 4	10
Thermal conductivity [W/cmK]	1.5	5	20
Yield [fC/MeV]	44.4	21.0	11.8
Sensitivity [pC/mGy/mm ³]	644	425	259
Wafer cost	O(<100€)	O(1,000€)	O(100,000€)*

- Wide bandgap energy
 - Not affected by T variations
 - Low leakage current
 - Transparent to visible light
- High atomic displacement threshold energy
 - Radiation hardness
- High saturation velocity and breakdown field
 - Timing
- **Good price-to-performance ratio**

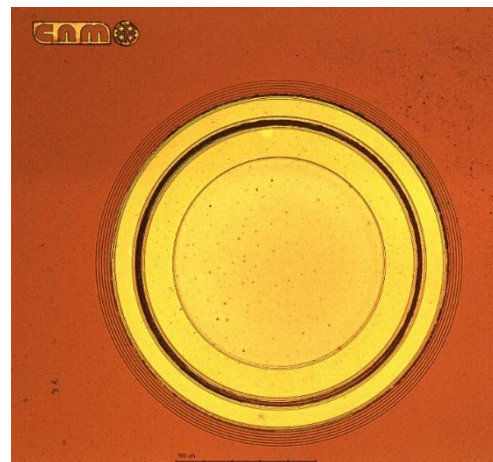
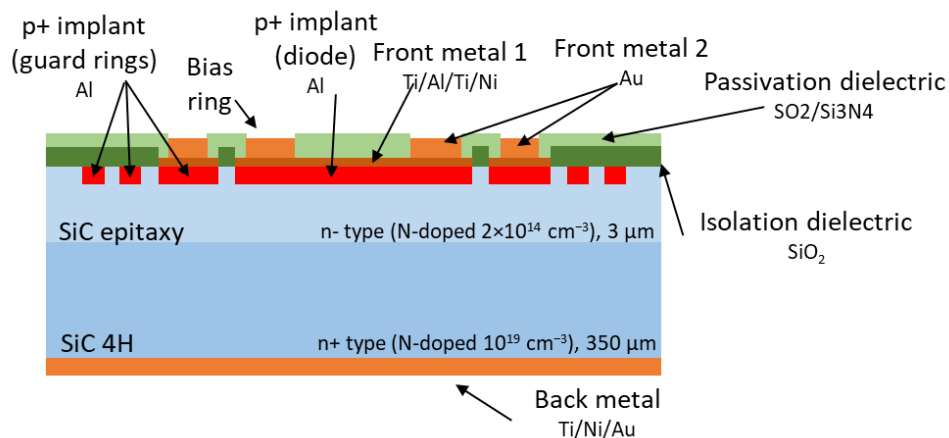
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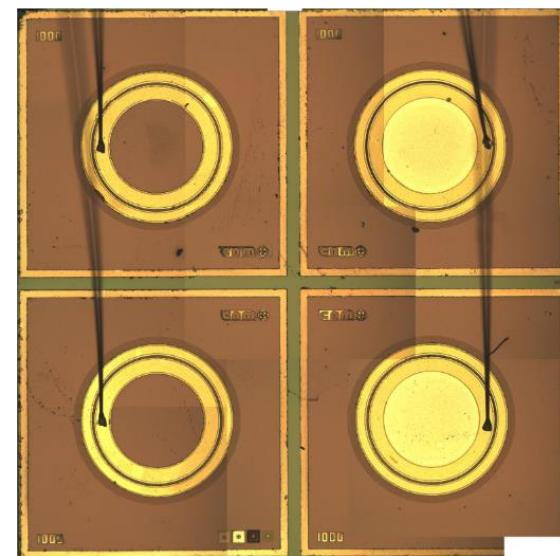
- P-N junction implanted diodes
- 4H-SiC, 100 mm wafers
- 3 μm high resistivity n-type doped epilayer
- **Operated without external bias, readout with electrometer**



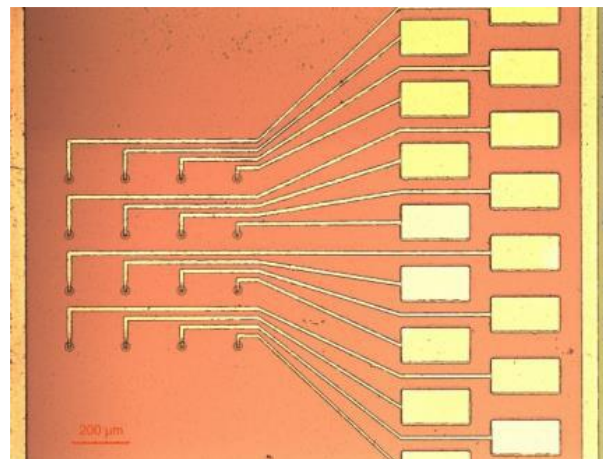
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2.2 mm diode



1 mm array



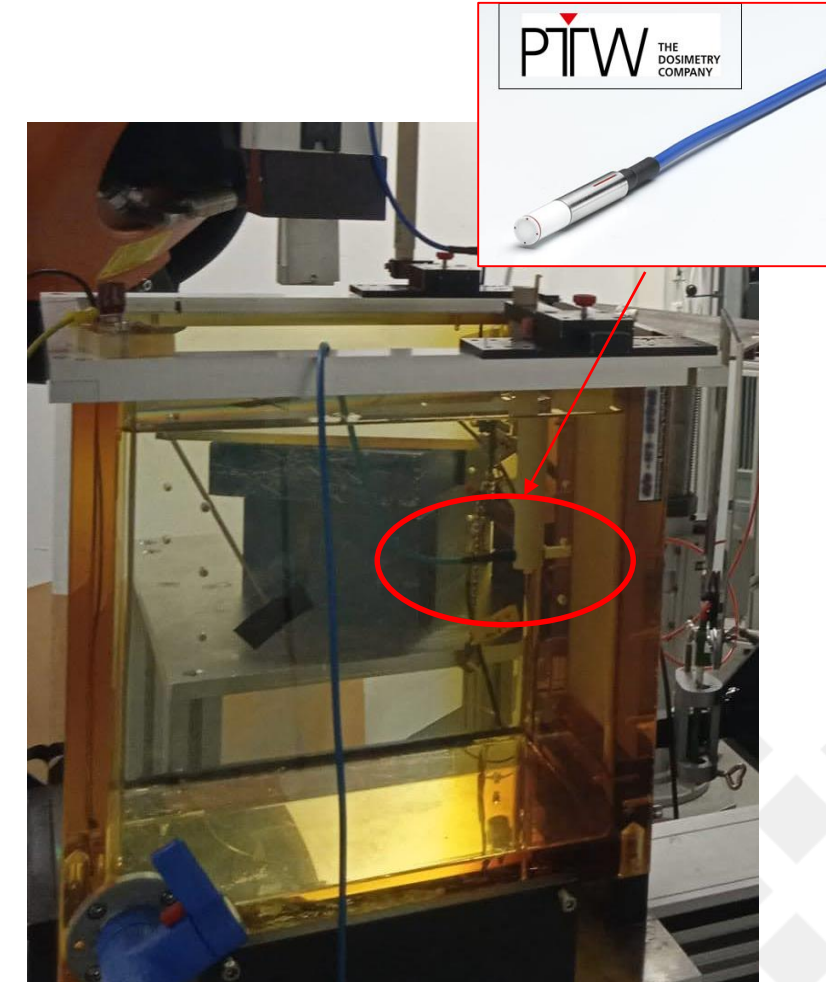
30 μm array

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- **20 MeV FLASH electrons** at PTB reference beam
- Reference dosimetry
 - Alanine
 - flashDiamond prototype (*M. Marinelli et al., Med Phys 2022*)
- **SiC diode**
 - 1 mm
 - Encapsulation by PTW

C. Fleta et al., Phys Med Biol 69 (2024) 095013

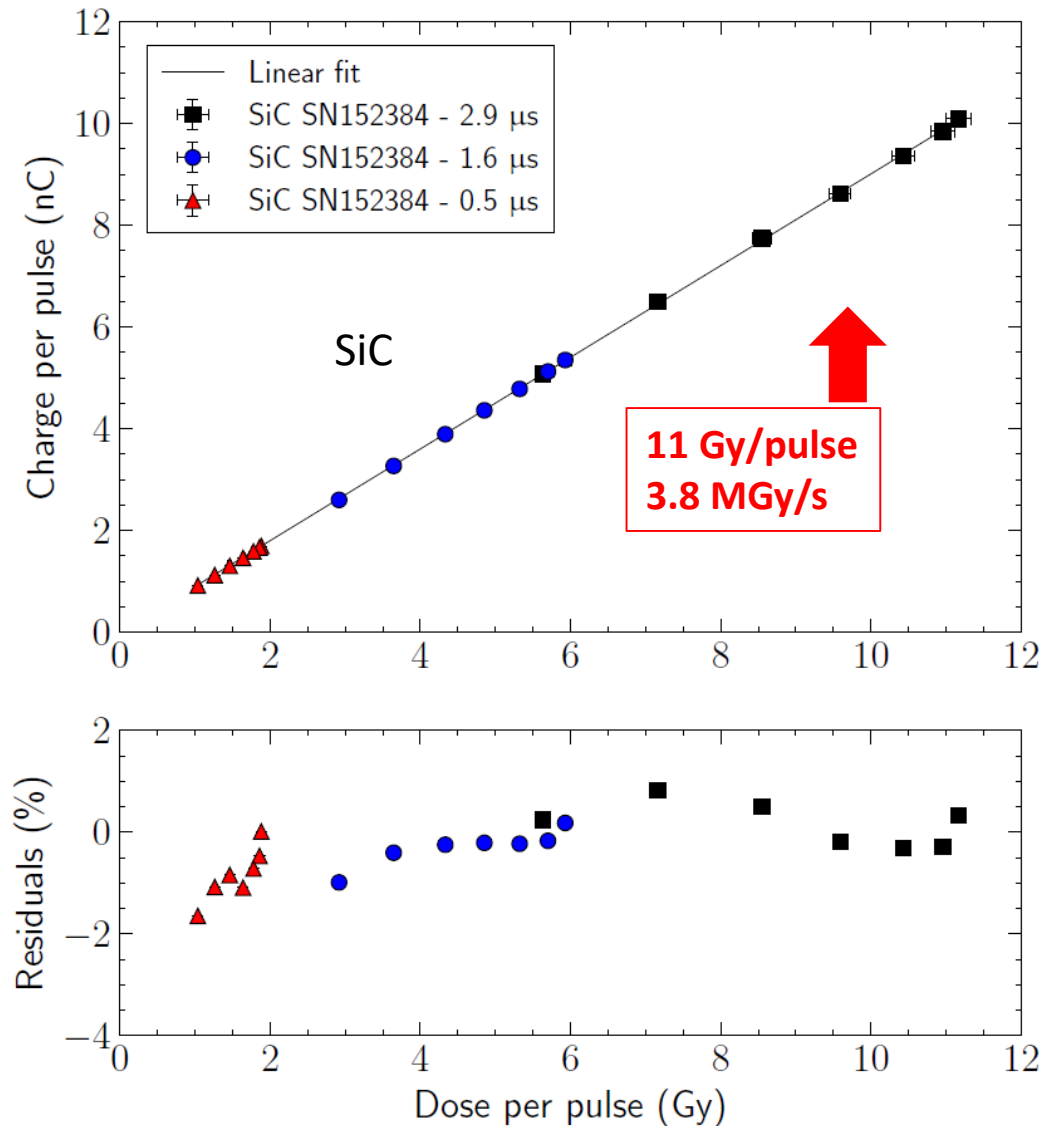


SiC diode in water phantom at PTB

Detector linearity

- Response independent both of DPP and of instantaneous dose rate
- Signal linearity **up to at least 11 Gy/pulse (3.8 MGy/s)** with a relative deviation of $< 3\%$ *

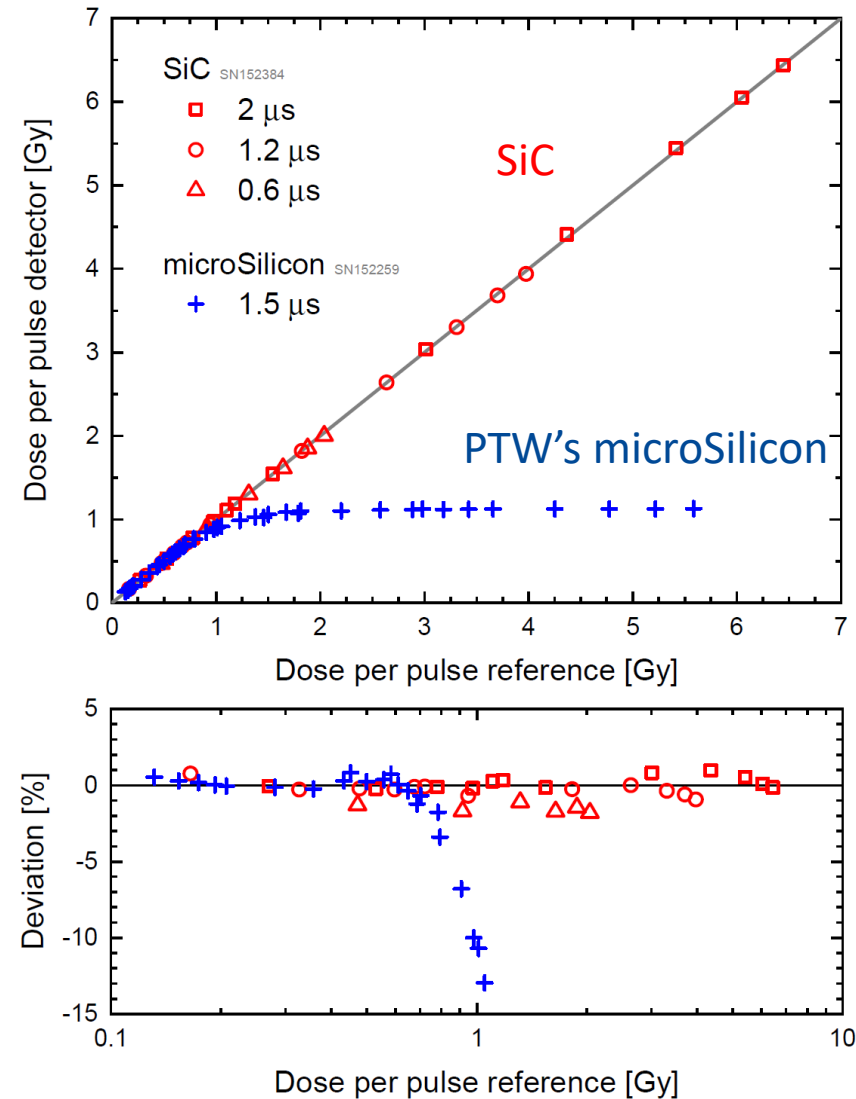
(*) includes uncertainty of reference detector



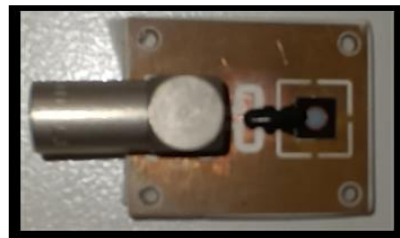
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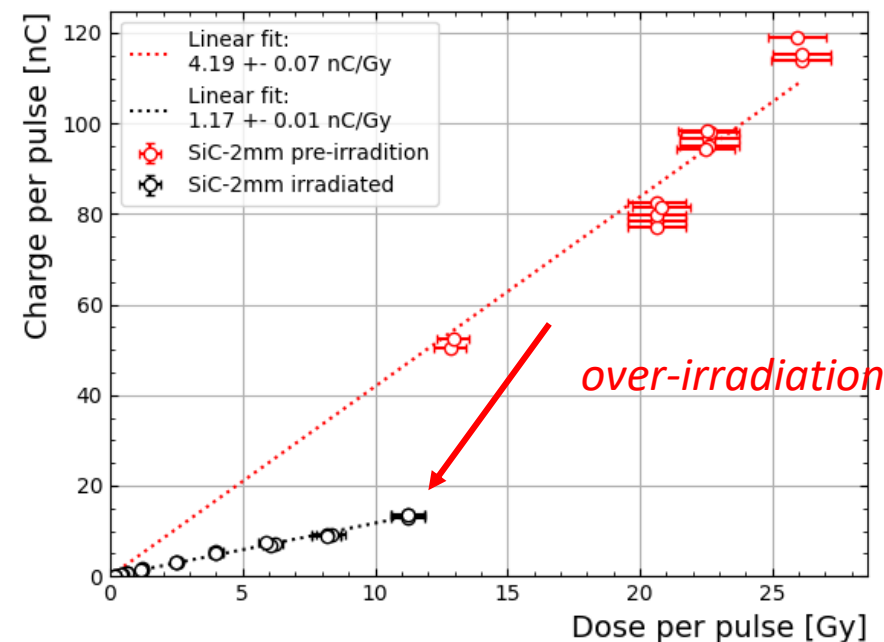
- **7 MeV protons** at CMAM
- FLASH beam structure: 20 μ s pulses, 1.54 ms inter-pulse
- Reference dosimetry EBT4



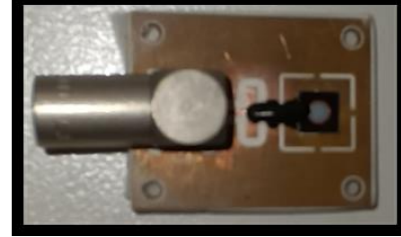
2.2 mm diode in PCB

Fresh diode:

- **Linear up to 26 Gy/pulse**



- **7 MeV protons** at CMAM
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- Reference dosimetry EBT4



2.2 mm diode in PCB

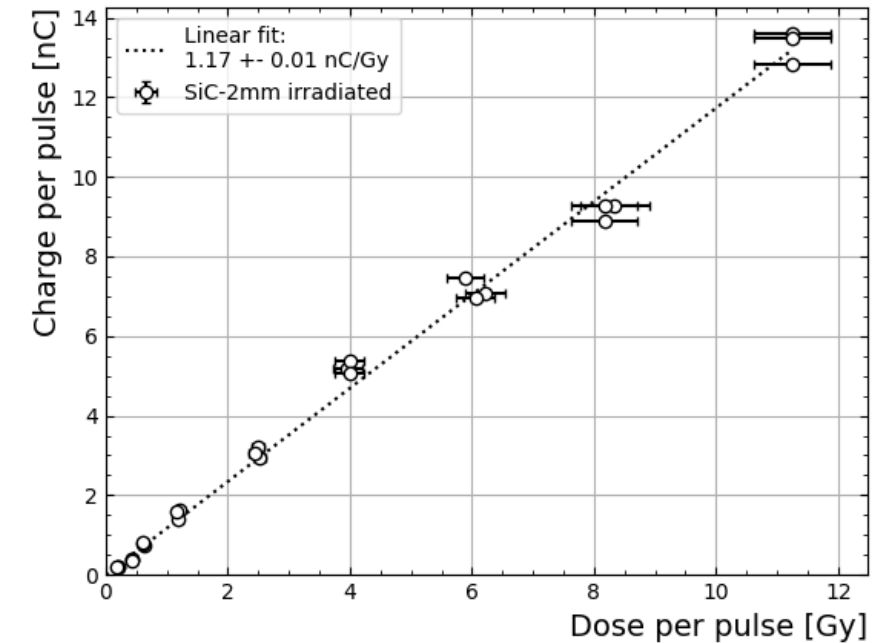
Fresh diode:

- **Linear up to 26 Gy/pulse**

After 52 kGy of 7 MeV protons:

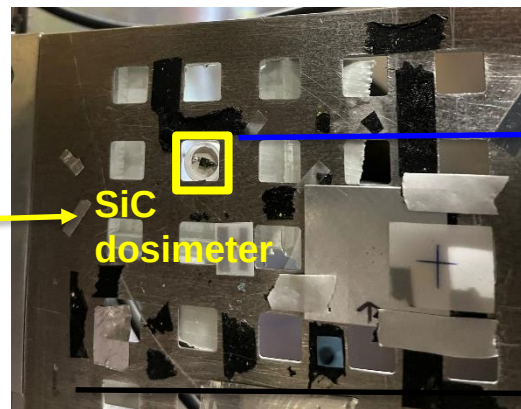
- Linearity is maintained up to at least 11 Gy/pulse

I. López-Paz et al., Med Phys 52:e17986 (2025)





Vacuum chamber



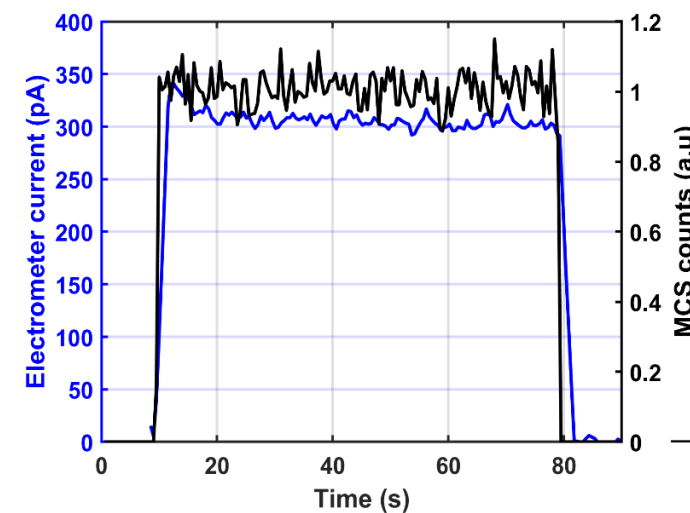
Sample holder

To Electrometer

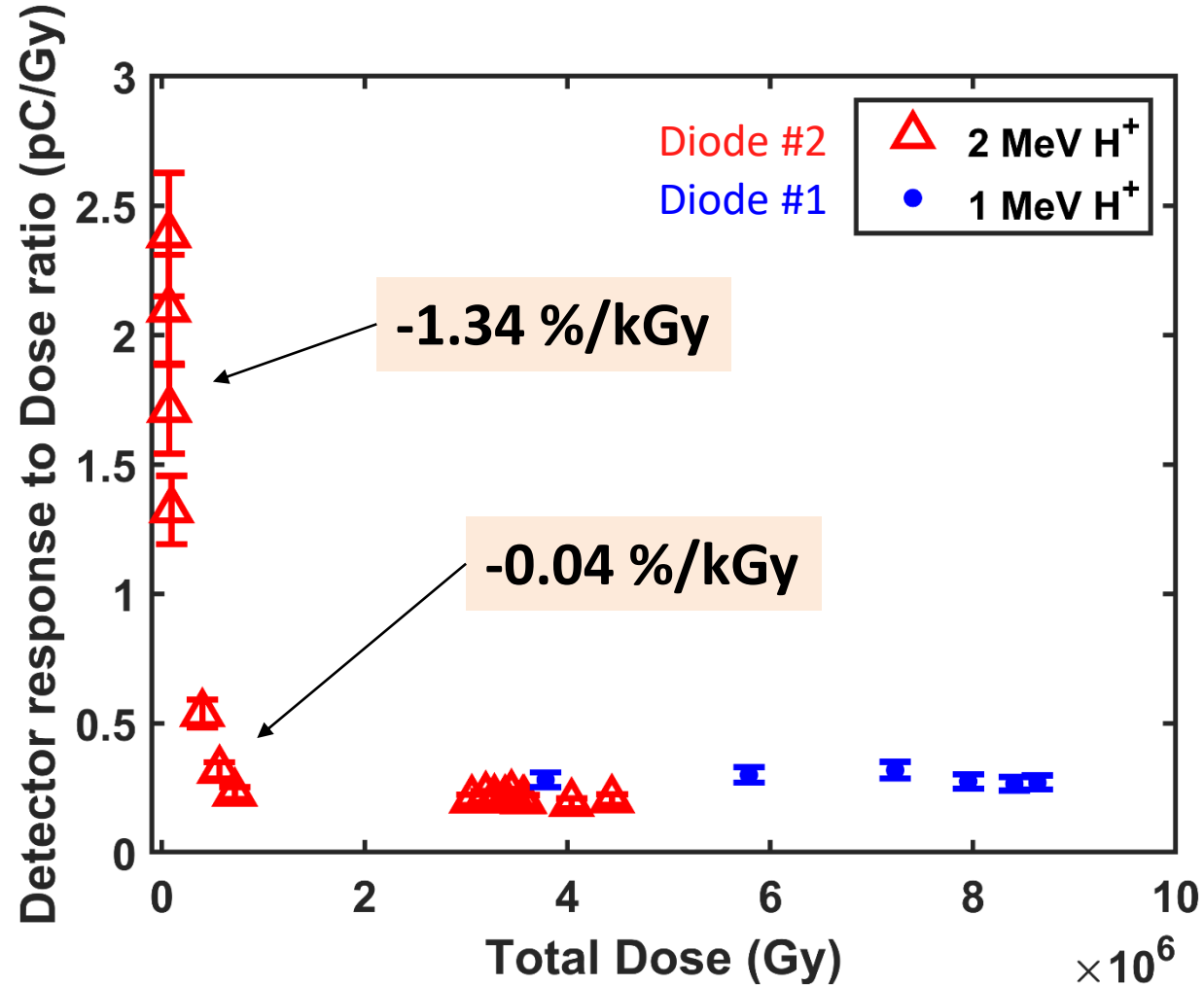
To Brookhaven
current
integrator

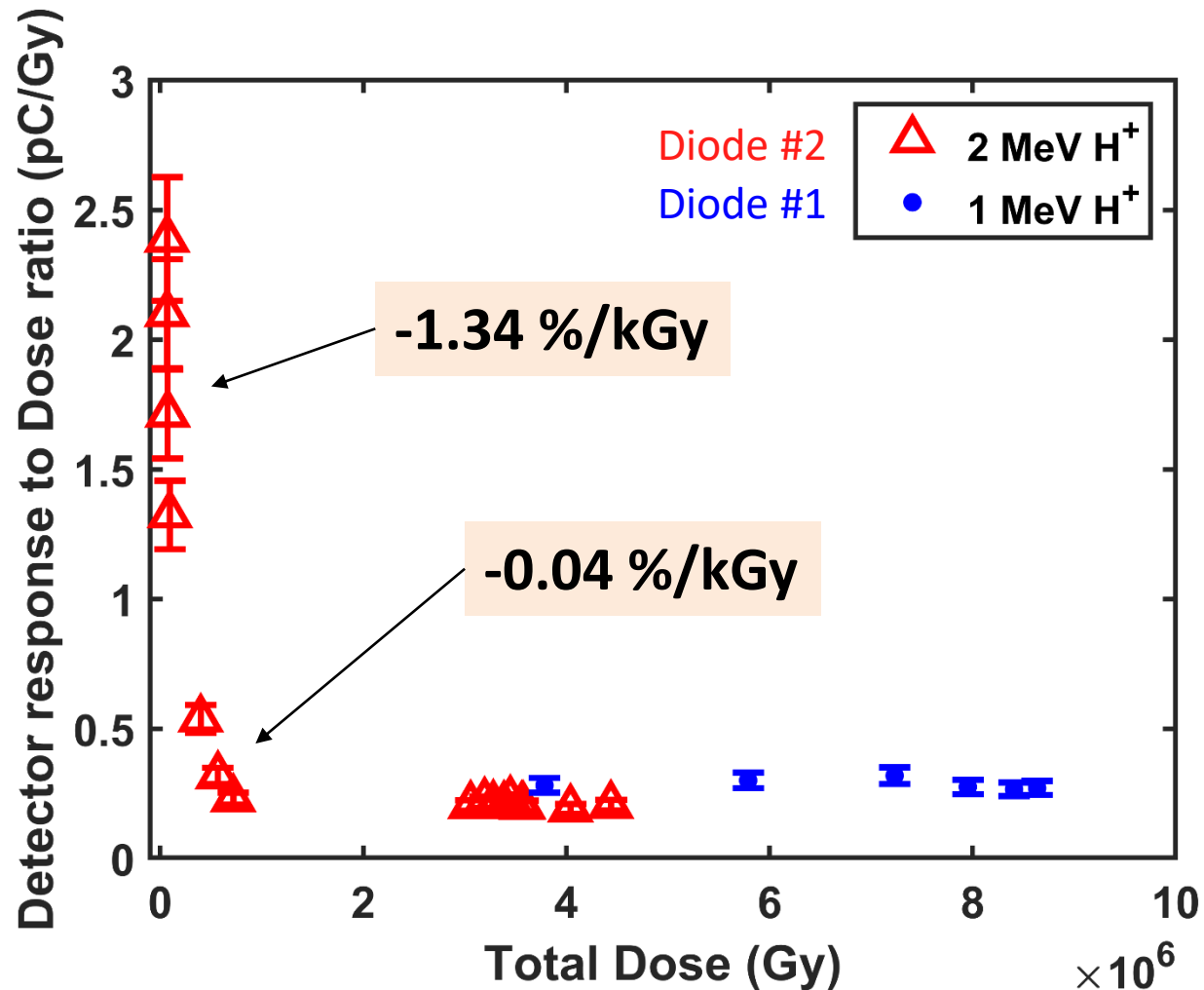
Pulsed beam current
measured to calculate dose

- **1 and 2 MeV protons** at CNA (Sevilla)
- FLASH beam structure: 1-10 μ s pulses, 500 Hz – 10 kHz, up to 5.6 Gy per pulse (4.6 MGy/s)
- 30 μ m diameter planar microdiodes

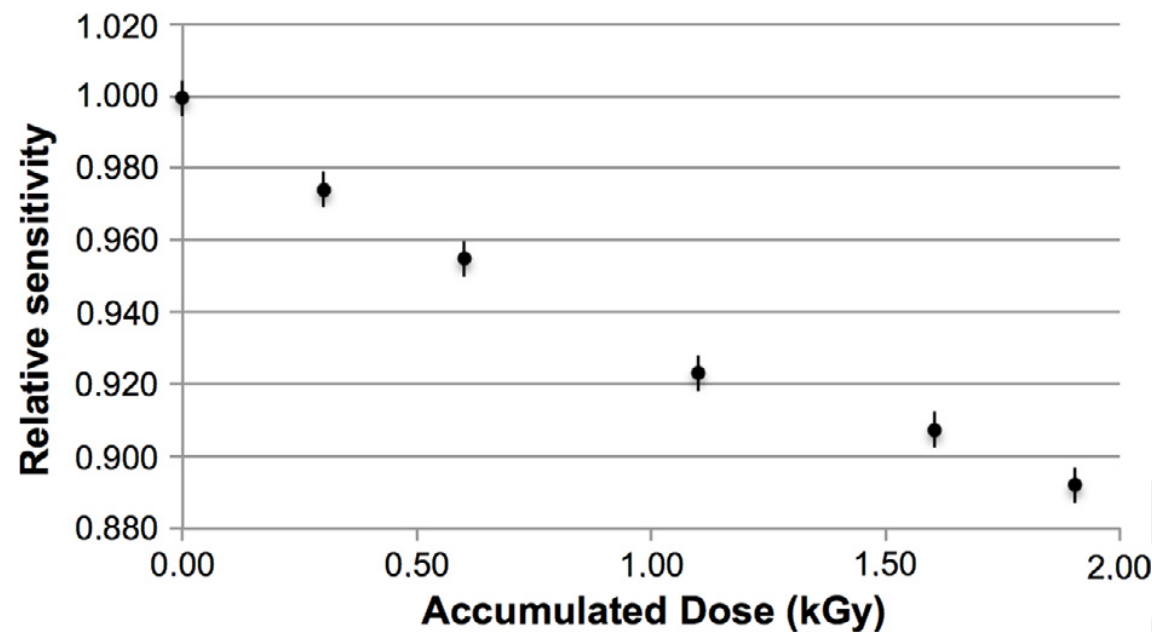


M.C. Jiménez-Ramos et al., IEEE Trans Radiat Plasma Med Sci (2025)

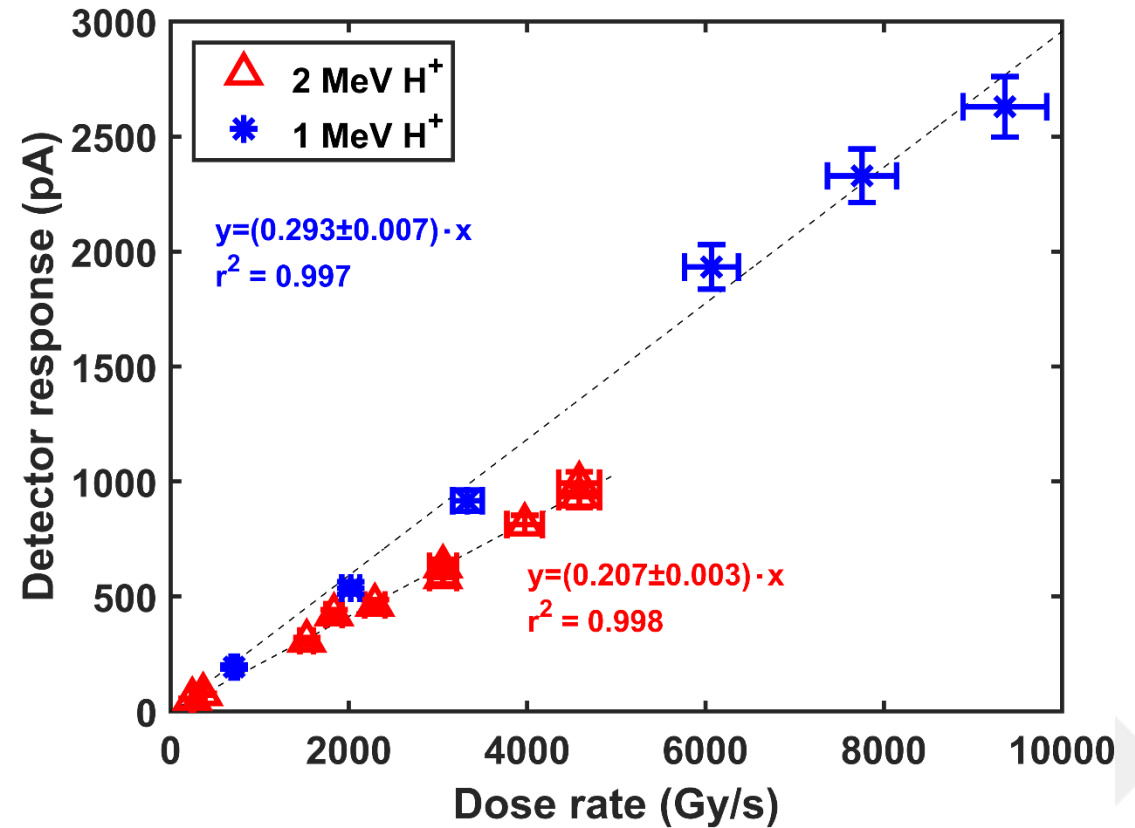
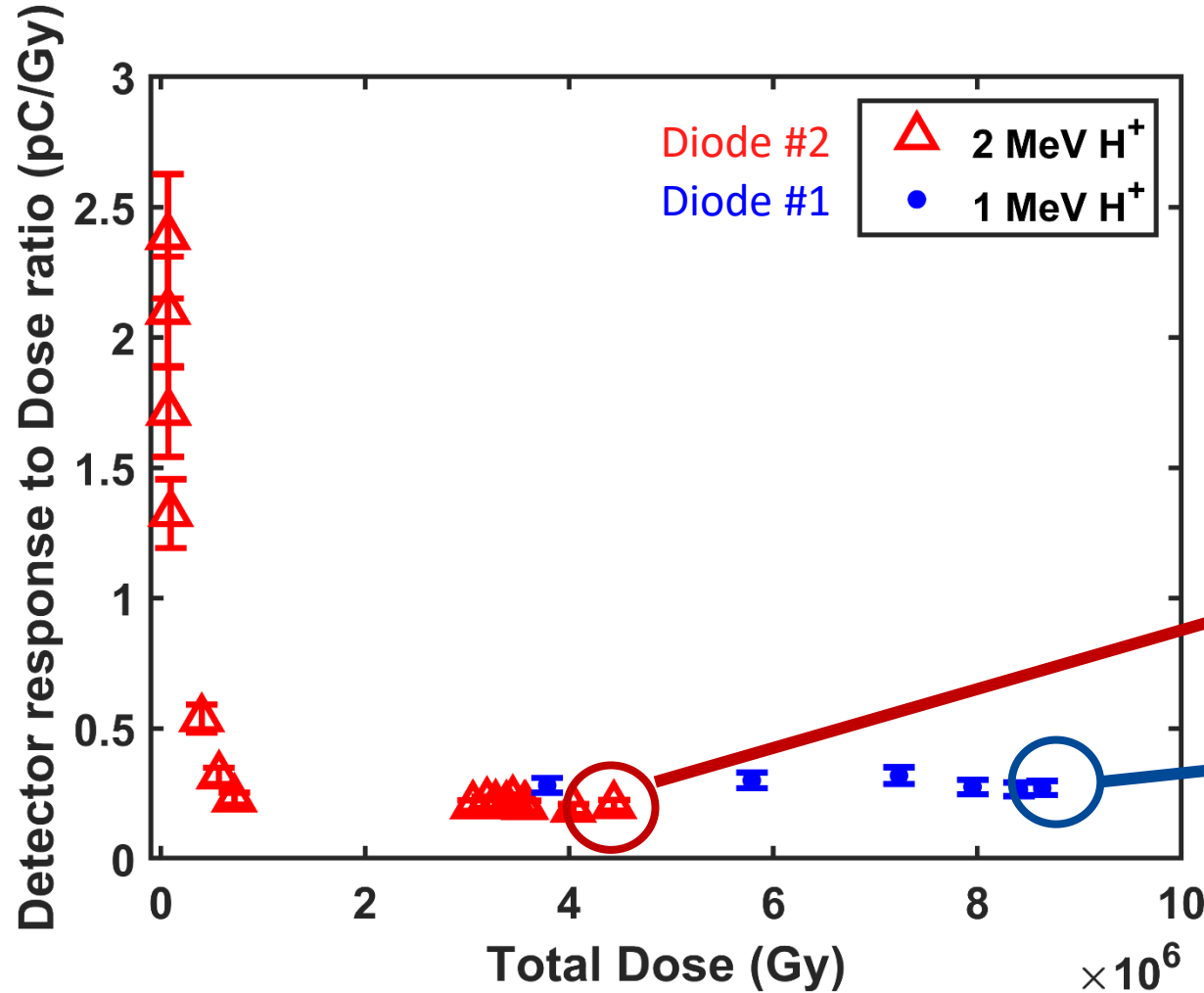




Commercial silicon dosimeter:
-5 %/kGy with 62MeV protons
NIEL/LET (62 MeV/2MeV) ≈ 1.3

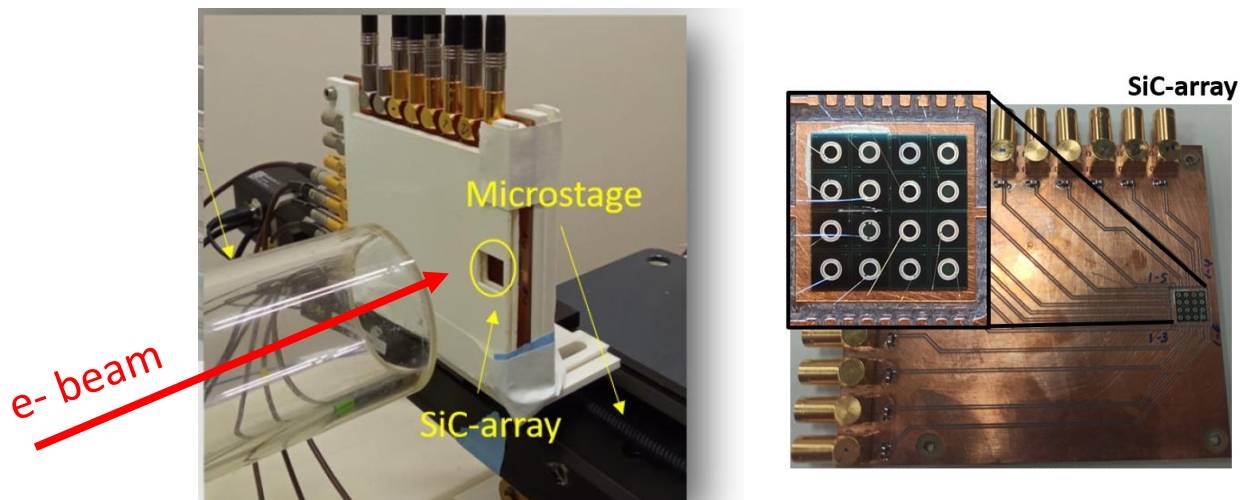


L. Raffaele et al., NIMA 891 (2018)



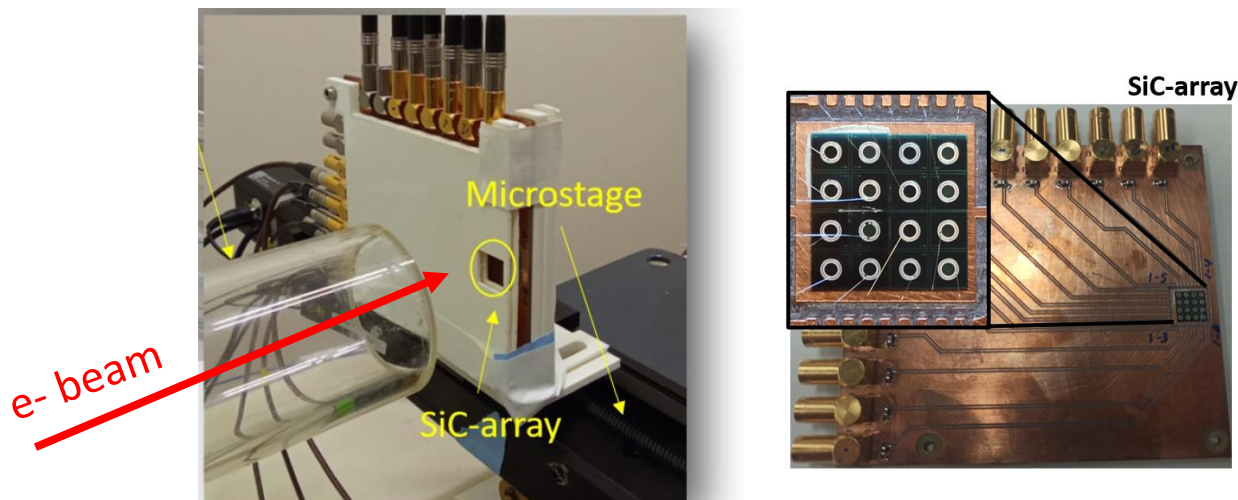
Linear behaviour for FLASH dose rates is maintained **after irradiation**

- **7 MeV e-FLASH** at Institut Curie (France)
- Pulses of 3 μ s, **6 Gy per pulse**
- 12-channel electrometer (PTW MultiDOS) adapted for UHDR
- 4x4 diode array (1 mm, pitch 2.2 mm)

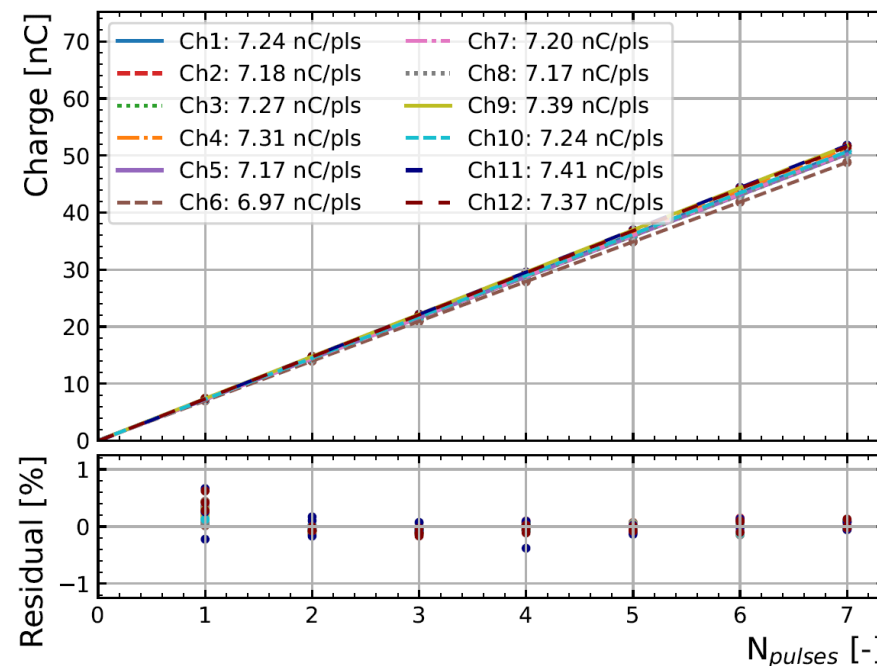


Iván López Paz et al., submitted to Med. Phys

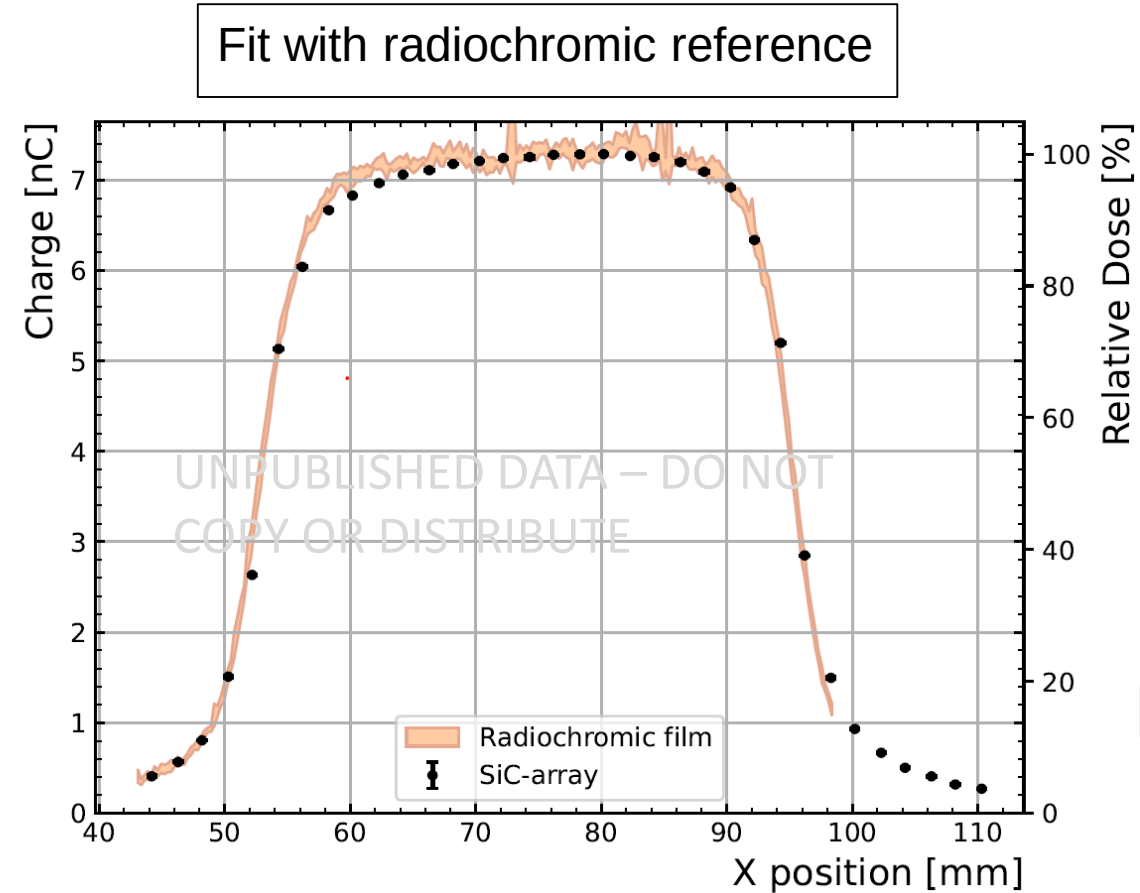
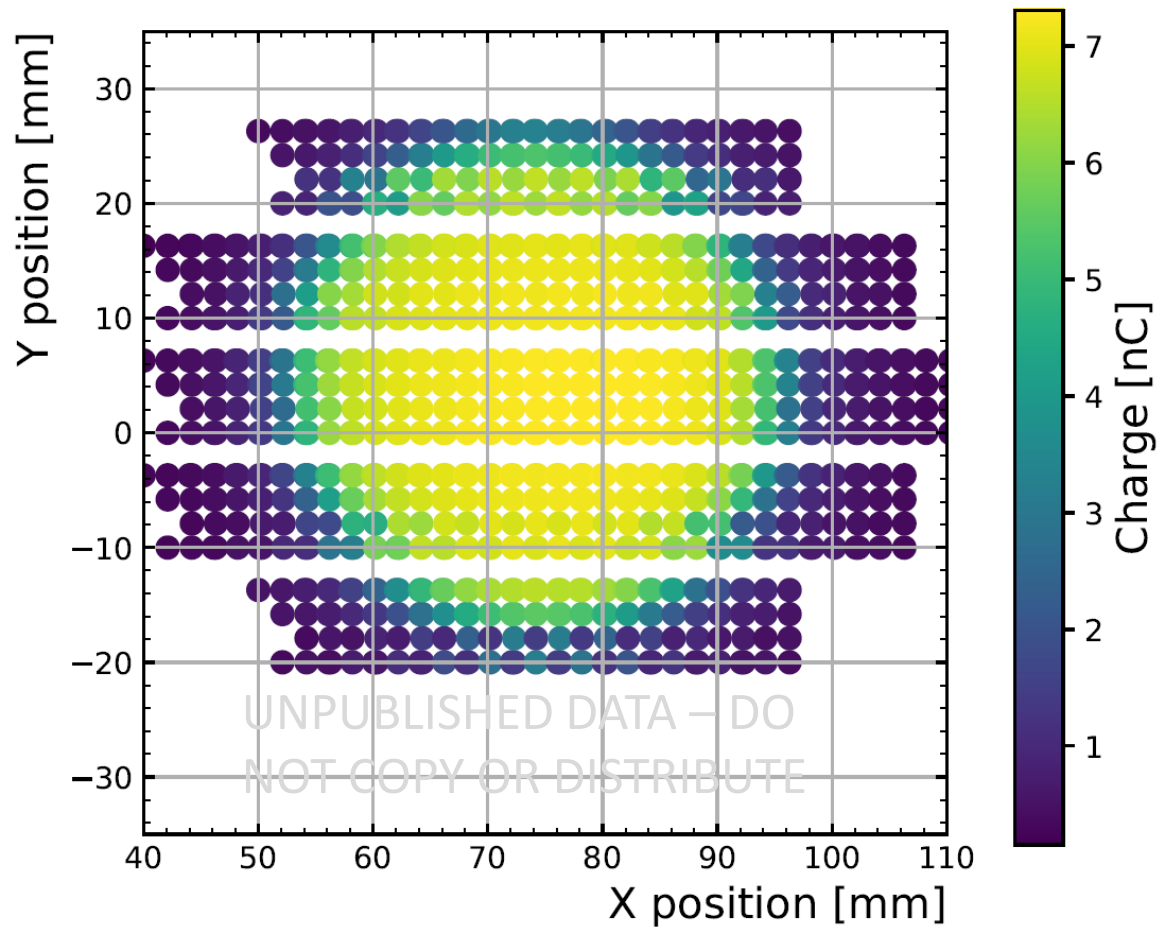
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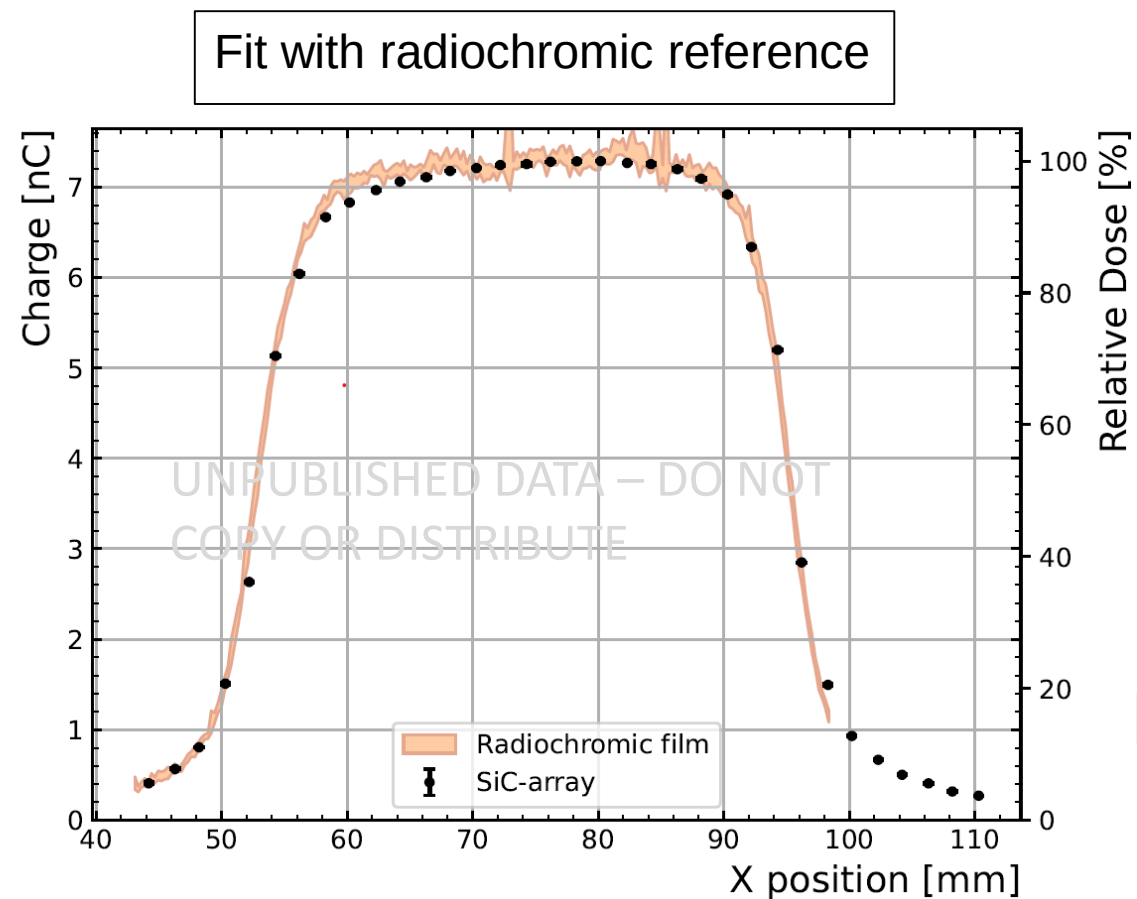
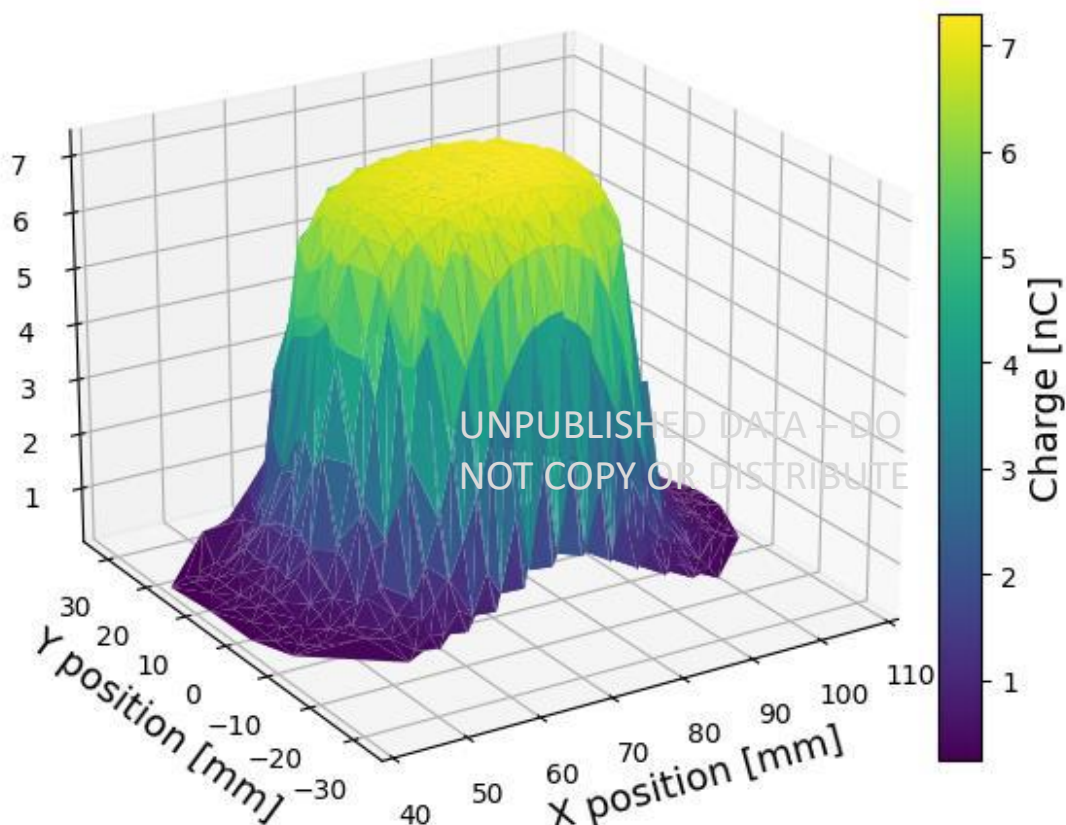


Iván López Paz et al., submitted to Med. Phys



- Sensitivity variation between pixels **< 4%**





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Conclusions

IMB-CNM have produced the first SiC diodes for relative dosimetry in ultra-high dose pulsed (FLASH) medical beams

- Operation without external bias
- Validated with UHDR electrons and protons
- Radiation hard + linear performance maintained after MGy doses
- Technological demonstrator of 2D dose monitor based on 4x4 array, [working towards a large SiC-based 2D dosimetry system \(0.6 mm diameter, 2 mm pitch, 20x20 cm² area coverage, custom readout\)](#)

Outlook

- Transmissive beam monitors
- SiC microdosimeters

Funding:

- ❖ UHDPulse: the EMPIR programme cofinanced by the Participating States and from the European Union's Horizon 2020 research and innovation program (18HLT04).
- ❖ NEWDOSI: Desarrollos tecnológicos para nuevos detectores de estado solido para dosimetría avanzada (PID2021-123484OB-I00).
- ❖ CARACTERIZACION: Caracterización de dosímetros avanzados fabricados en el IMB-CNM para aplicaciones médicas (202250I185).
- ❖ Microdetectors for medical applications. Proyectos Intramurales Especiales CSIC (20225AT008).
- ❖ Dosimetry monitor for FLASH therapy. LaCaixa foundation (HR23-00718)



Collaborators:

Andreas Schüller (PTB), Rafael Kranzer (PTW)

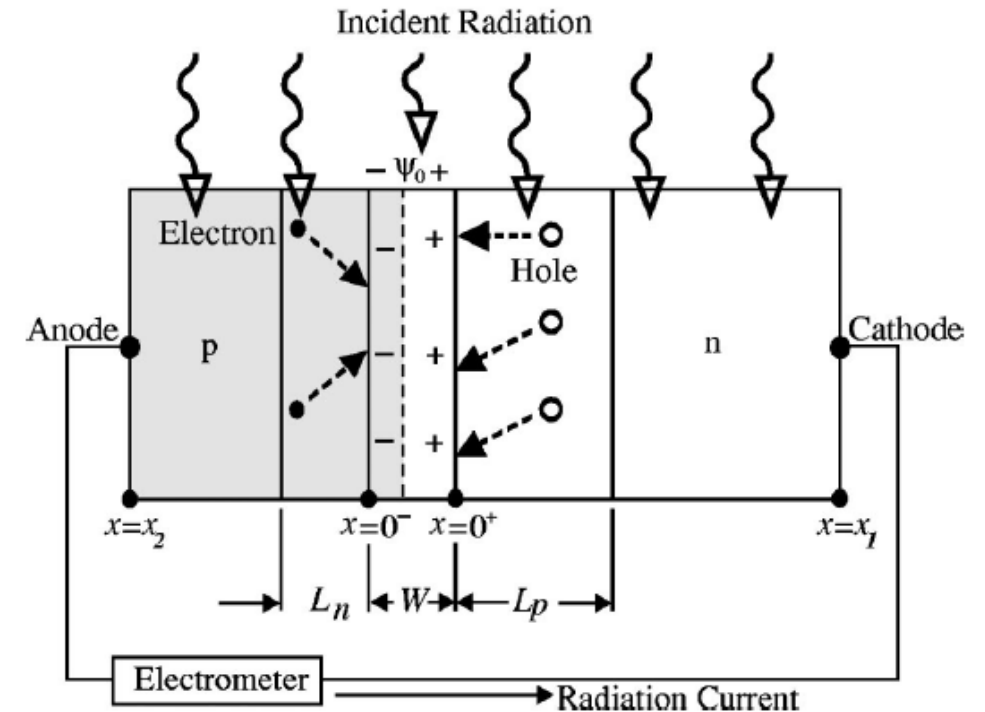
Paula Ibáñez, Daniel Sanchez-Parcerisa, Adrián Zazpe, Inés del Monte (Universidad Complutense de Madrid)

Thanks for your attention

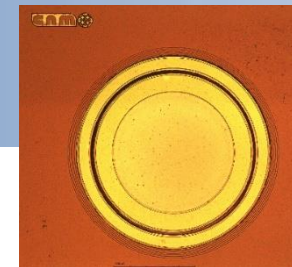
 Celeste.Fleta@csic.es

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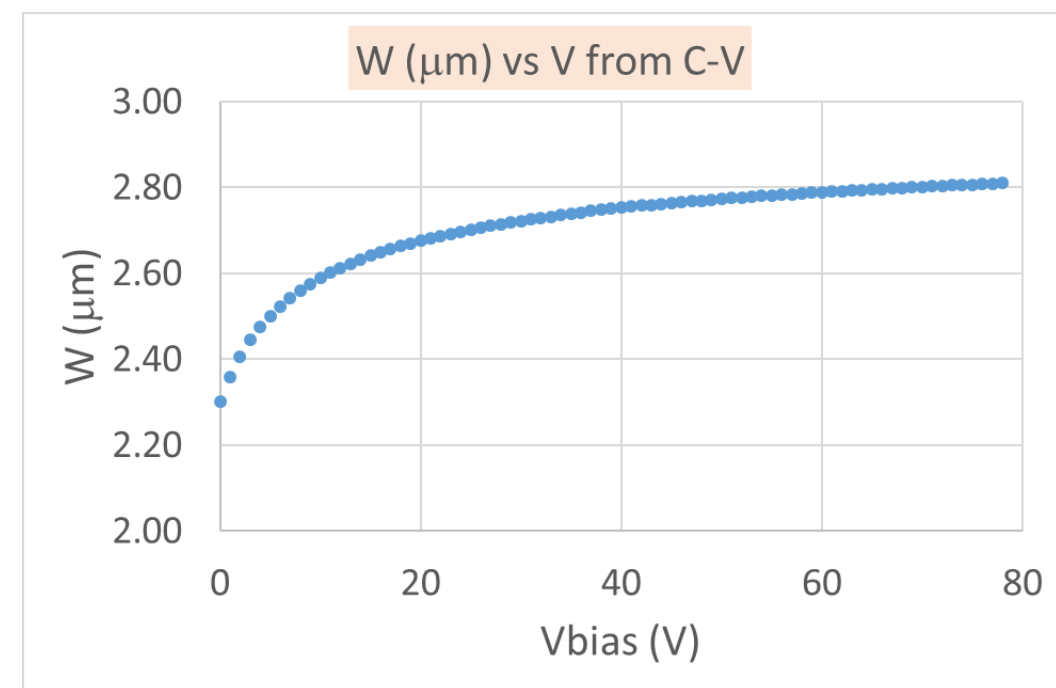
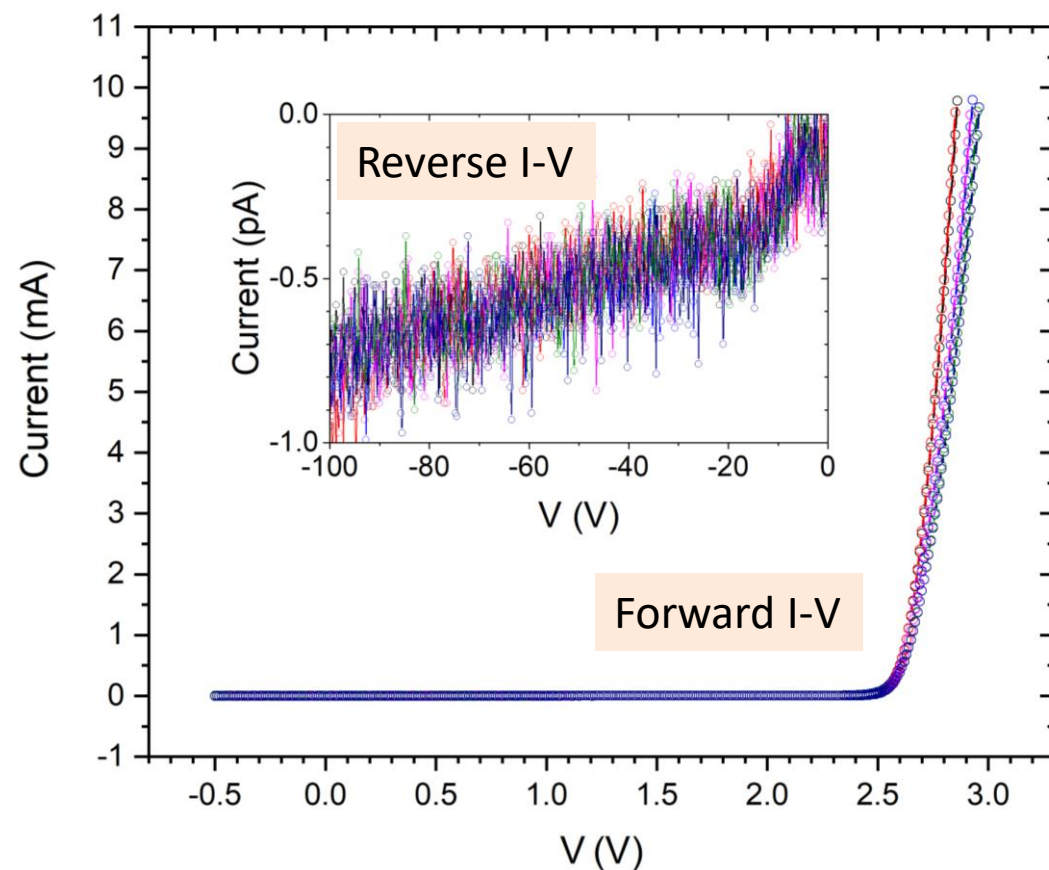
- p–n (or Schottky) junction in:
 - Current mode operation
 - Unbiased conditions
- The radiation-induced current is measured by an electrometer
- The current is proportional to the dose rate and its integration provides the absorbed dose in the semiconductor



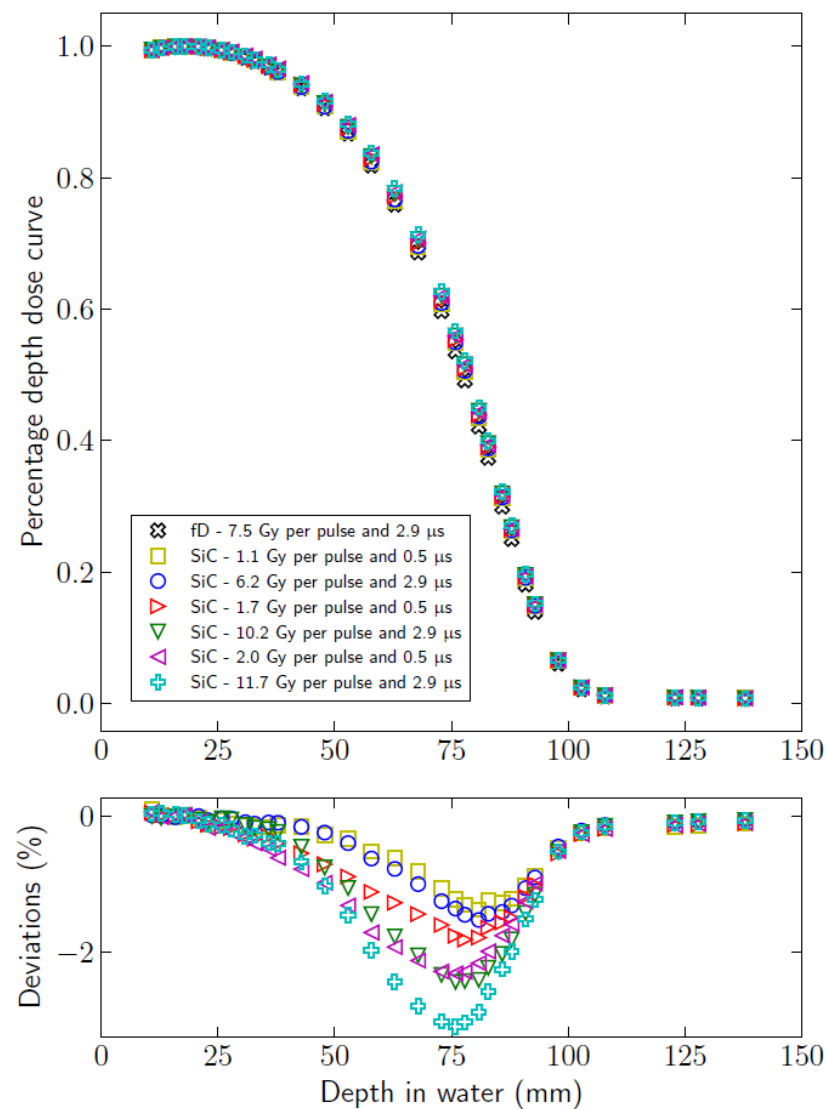
Shi et al., Med Phys 30 (2003)



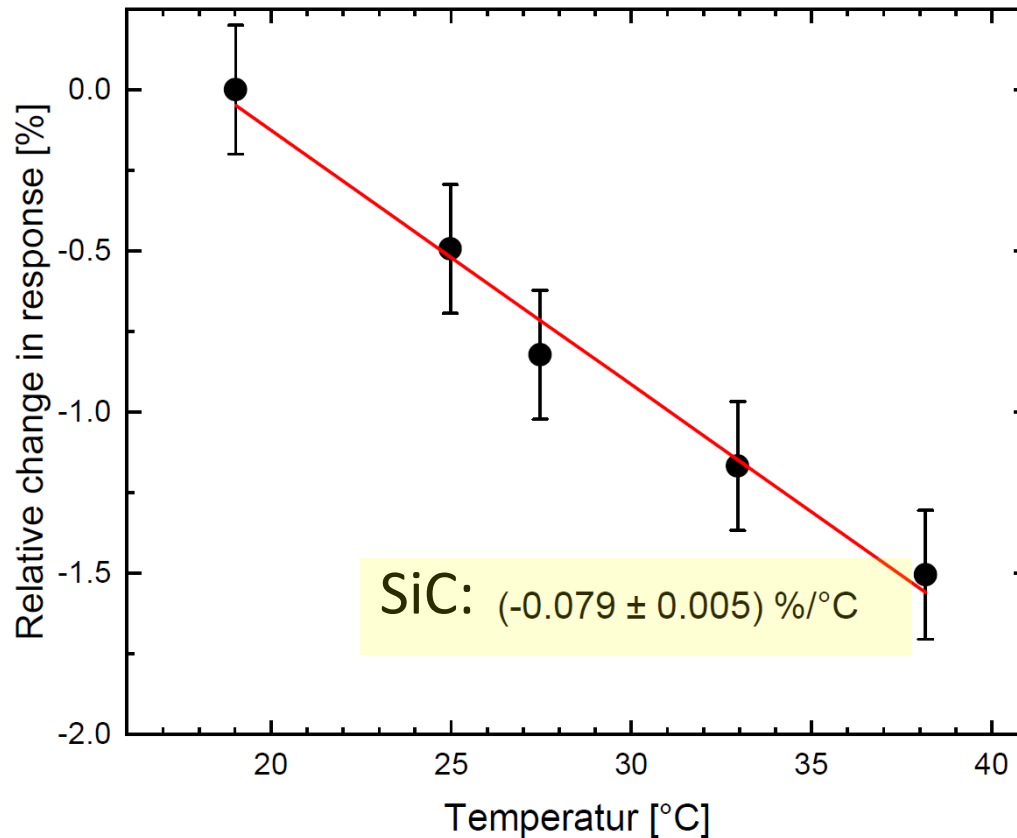
Large single diodes



PDD measurement in UHDR conditions



Temperature dependence of sensitivity



- Sensitivity reduction of **$-0.08\% / ^\circ\text{C}$**
- Better than most commercial Si diodes + opposite trend

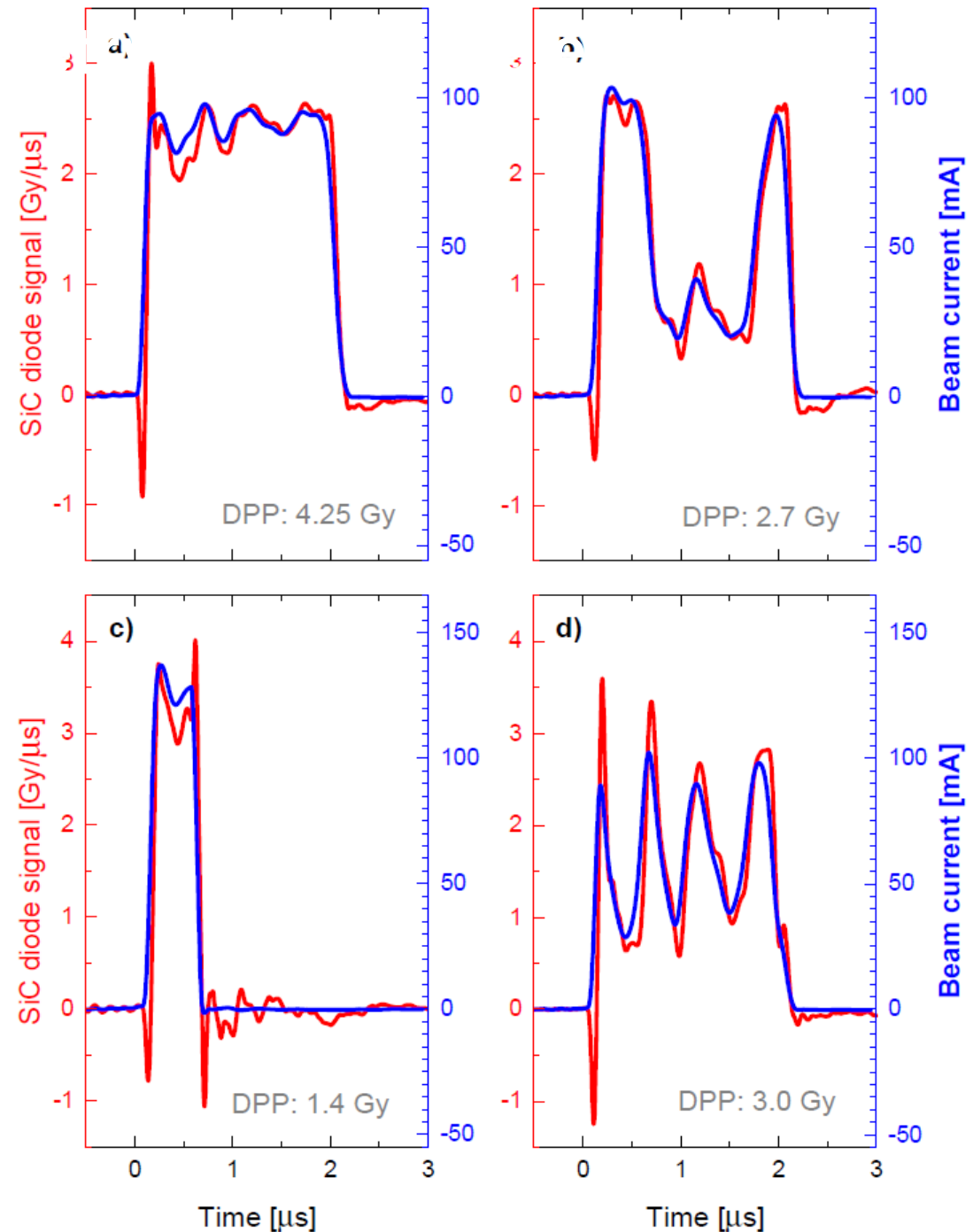
TABLE III. Temperature coefficients for *n*- and *p*-type diodes. All measurement were made at depth of 5 cm, $10 \times 10 \text{ cm}^2$, SSD= 100 cm.

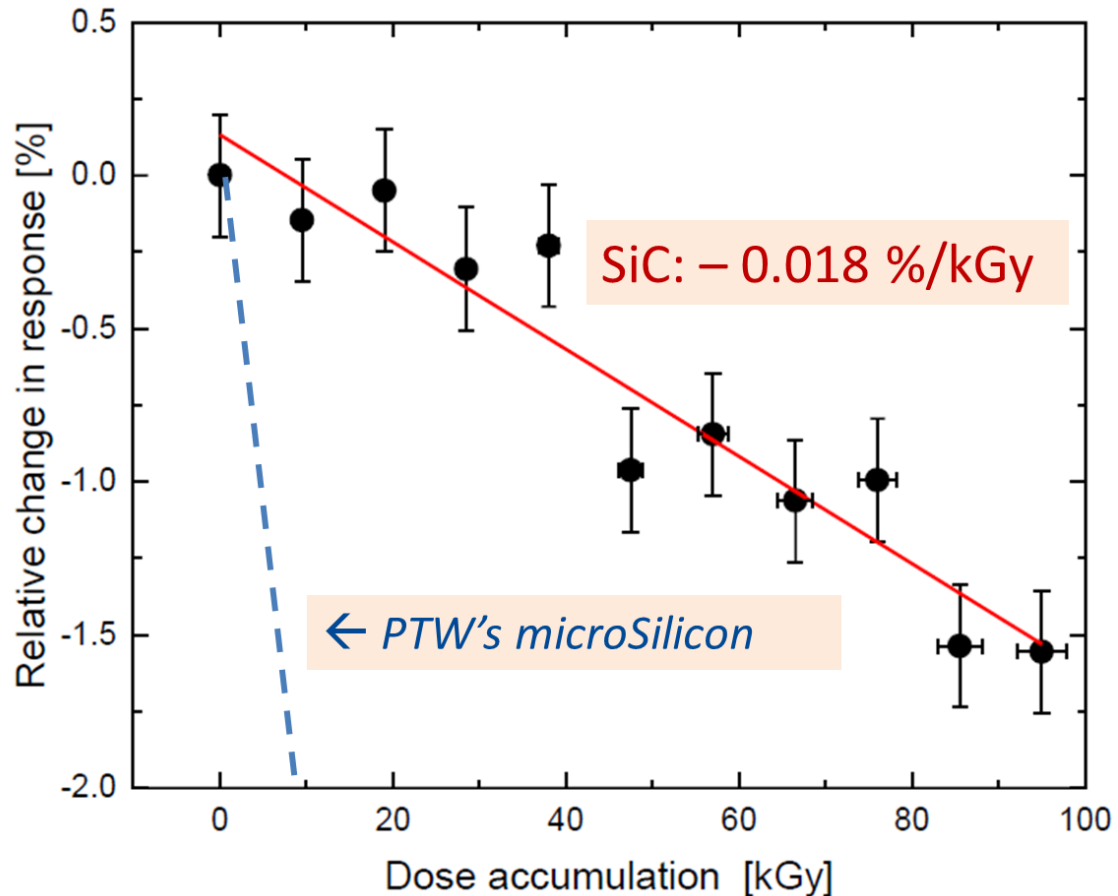
Diode type	Temperature coefficient		
	6 MV (%/°C)	15 or 20 MV (%/°C)	Co-60 (%/°C)
Isorad Gold 1, unirradiated	0.06	0.05 (20 MV)	0.45 (T1000)
Isorad Gold 2, unirradiated	0.08	0.10 (20 MV)	0.16 (T1000)
Isorad Red	0.22	0.21 (20 MV)	0.37 (T1000)
QED unirradiated	0.27	0.25 (15 MV)	0.34 (TPhoenix)
QED Blue Diode	0.30	0.31 (15 MV)	0.30 (T780)
QED Red Diode	0.29	0.29 (15 MV)	0.29 (T780)
Scanditronix EDP 10	0.38	0.33 (20 MV)	0.36 (T1000)
Scanditronix EDP 30	0.36	0.34 (20 MV)	0.39 (T1000)

A. S. Saini and T. C. Zhu, Med Phys 29 (2002)

Time-resolved signals

- The SiC diode is capable of effectively tracking the beam pulse current in FLASH conditions





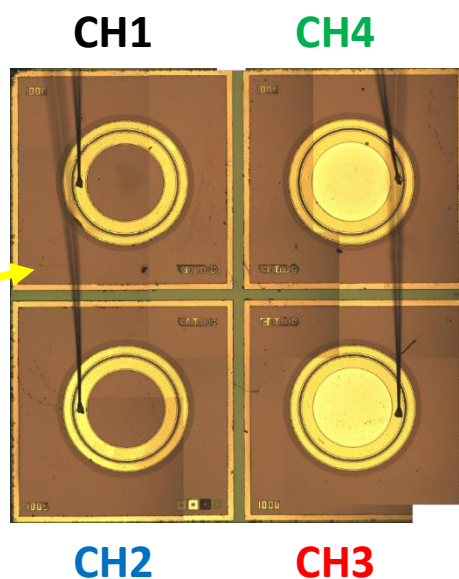
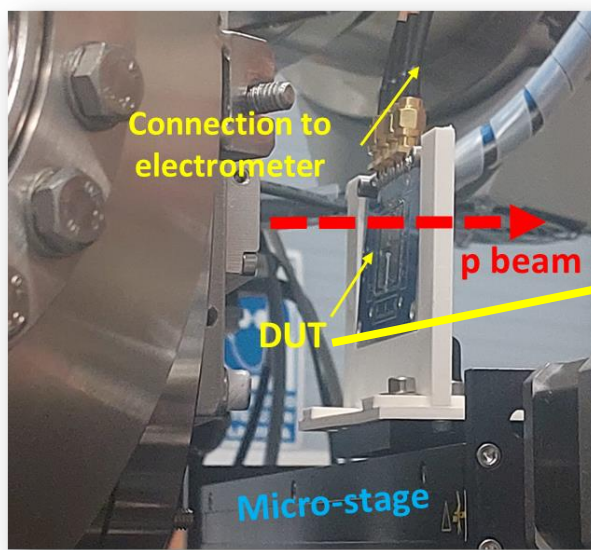
(initial irradiation of SiC diode (10s kGy) not shown)

Long-term radiation hardness

- Linear decrease of sensitivity of **0.018% / kGy** of 20 MeV electrons
 → Not as radiation hard as diamond, **much better than commercial silicon diodes**

Position-resolved measurements

- Measured beam profiles match with radiochromic film
- Viability of a pixel array beam monitor for QA



4-channel array of 1 mm diodes

